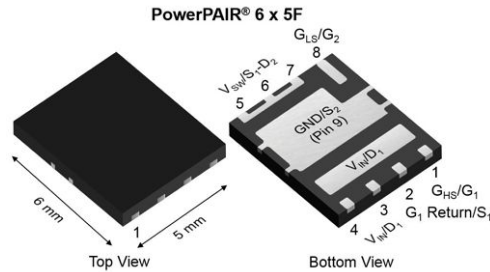


Dual N-Channel 30 V (D-S) MOSFET with Schottky Diode



FEATURES

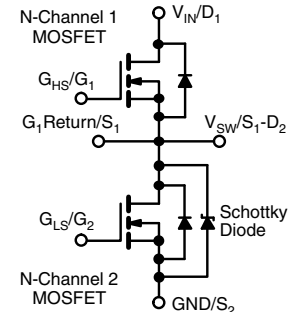
- TrenchFET® Gen IV power MOSFET
- SkyFET® low side MOSFET with integrated Schottky
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- CPU core power
- Computer / server peripherals
- POL
- Synchronous buck converter
- Telecom DC/DC



PRODUCT SUMMARY		
	CHANNEL-1	CHANNEL-2
V _{DS} (V)	30	30
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.00210	0.00068
R _{DS(on)} max. (Ω) at V _{GS} = 4.5 V	0.00370	0.00130
Q _g typ. (nC)	11.7	38
I _D (A) ^a	105	257
Configuration	Dual	

ORDERING INFORMATION

Package	PowerPAIR 6 x 5F
Lead (Pb)-free and halogen-free	SiZF906BDT-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	CHANNEL-1	CHANNEL-2	UNIT	
Drain-source voltage	V _{DS}	30	30	V	
Gate-source voltage	V _{GS}	+20, -16	+20, -16	V	
Continuous drain current (T _J = 150 °C)	I _D	T _C = 25 °C	105	257	A
		T _C = 70 °C	84	206	
		T _A = 25 °C	36 ^{b, c}	63 ^{b, c}	
		T _A = 70 °C	29 ^{b, c}	50 ^{b, c}	
Pulsed drain current (t = 100 μs)	I _{DM}	120	350	A	
Continuous source-drain diode current	I _S	T _C = 25 °C	34	141 ^a	A
		T _A = 25 °C	4.1 ^{b, c}	8.5 ^{b, c}	
Single pulse avalanche current	I _{AS}	23	40	A	
Single pulse avalanche energy	E _{AS}	26.5	80	mJ	
Maximum power dissipation	P _D	T _C = 25 °C	38	83	W
		T _C = 70 °C	24	53	
		T _A = 25 °C	4.5 ^{b, c}	5 ^{b, c}	
		T _A = 70 °C	2.9 ^{b, c}	3.2 ^{b, c}	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150		°C	
Soldering recommendations (peak temperature) ^{d, e}		260		°C	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	CHANNEL-1		CHANNEL-2		UNIT	
		TYP.	MAX.	TYP.	MAX.		
Maximum junction-to-ambient ^{b, f}	t ≤ 10 s	R _{thJA}	22	28	20	25	°C/W
Maximum junction-to-case (source)	Steady state	R _{thJC}	2.6	3.3	1.2	1.5	°C/W

Notes

- T_C = 25 °C
- Surface mounted on 1" x 1" FR4 board
- t = 20 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 60 °C/W for channel-1 and 60 °C/W for channel-2



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Ch-1	30	-	-	V	
		$V_{GS} = 0\text{ V}, I_D = 5\text{ mA}$	Ch-2	30	-	-		
Drain-source breakdown voltage ^c (transient)	V_{DSt}	$V_{GS} = 0\text{ V}, t_{(transient)} \leq 1\text{ }\mu\text{s}$	Ch-1	36	-	-		
			Ch-2	36	-	-		
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1.1	-	2.2		
			Ch-2	1.1	-	2.2		
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = +20\text{ V}, -16\text{ V}$	Ch-1	-	-	± 100	nA	
			Ch-2	-	-	± 100		
Zero Gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1	-	-	1	μA	
			Ch-2	-	100	1000		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	Ch-1	-	-	5		
			Ch-2	-	500	5000		
On-state drain current ^b	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20	-	-	A	
			Ch-2	20	-	-		
Drain-source on-state resistance ^b	$R_{DS(on)}$		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	Ch-1	-	0.00150	0.00210	Ω
			$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	Ch-2	-	0.00045	0.00068	
			$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-1	-	0.00250	0.00370	
			$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$	Ch-2	-	0.00085	0.00130	
Forward transconductance ^b	g_{fs}		$V_{DS} = 10\text{ V}, I_D = 40\text{ A}$	Ch-1	-	93	-	S
			$V_{DS} = 10\text{ V}, I_D = 30\text{ A}$	Ch-2	-	170	-	
Dynamic ^a								
Input capacitance	C_{iss}	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1	-	1630	-	pF	
Output capacitance	C_{oss}		Ch-2	-	5550	-		
			Ch-1	-	690	-		
Reverse transfer capacitance	C_{rss}		Ch-2	-	2320	-		
			Ch-1	-	50	-		
C_{rss}/C_{iss} ratio			Ch-1	-	0.030	0.060		
		Ch-2	-	0.037	0.080			
Total gate charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	Ch-1	-	25	49	nC	
			Ch-2	-	81	165		
Gate-source charge	Q_{gs}	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$	Ch-1	-	11.7	22		
			Ch-2	-	38	80		
Gate-drain charge	Q_{gd}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$	Ch-1	-	5.8	-		
			Ch-2	-	17.8	-		
Output charge	Q_{oss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$	Ch-1	-	2.9	-		
			Ch-2	-	8.4	-		
Gate resistance	R_g	$f = 1\text{ MHz}$	Ch-1	0.2	1.2	2	Ω	
			Ch-2	0.12	0.6	1.2		



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Dynamic ^a							
Turn-on delay time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}, R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$	Ch-1	-	22	40	ns
Rise time	t_r		Ch-2	-	40	80	
Turn-off delay time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}, R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$	Ch-1	-	75	150	
			Ch-2	-	130	260	
Fall time	t_f	Channel-1	Ch-1	-	21	40	
			Ch-2	-	41	80	
Turn-on delay time	$t_{d(on)}$	Channel-2	Ch-1	-	10	20	
			Ch-2	-	20	40	
Rise time	t_r	Channel-1 $V_{DD} = 15\text{ V}, R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$	Ch-1	-	12	20	
			Ch-2	-	20	40	
Turn-off delay time	$t_{d(off)}$	Channel-2	Ch-1	-	5	10	
			Ch-2	-	30	60	
Fall time	t_f	Channel-1	Ch-1	-	22	40	
			Ch-2	-	40	80	
		Channel-2	Ch-1	-	5	10	
			Ch-2	-	10	20	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	$T_C = 25\text{ }^\circ\text{C}$	Ch-1	-	-	34	A
			Ch-2	-	-	141	
Pulse diode forward current ^a	I_{SM}		Ch-1	-	-	120	
			Ch-2	-	-	350	
Body diode voltage	V_{SD}	$I_S = 10\text{ A}, V_{GS} = 0\text{ V}$	Ch-1	-	0.8	1.1	V
		$I_S = 5\text{ A}, V_{GS} = 0\text{ V}$	Ch-2	-	0.39	0.59	
Body diode reverse recovery time	t_{rr}	Channel-1 $I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ $T_J = 25\text{ }^\circ\text{C}$	Ch-1	-	27	55	ns
			Ch-2	-	55	110	
Body diode reverse recovery charge	Q_{rr}	Channel-2 $I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ $T_J = 25\text{ }^\circ\text{C}$	Ch-1	-	17	35	nC
			Ch-2	-	65	130	
Reverse recovery fall time	t_a	Channel-1	Ch-1	-	15	-	ns
			Ch-2	-	31	-	
Reverse recovery rise time	t_b	Channel-2	Ch-1	-	12	-	
			Ch-2	-	24	-	

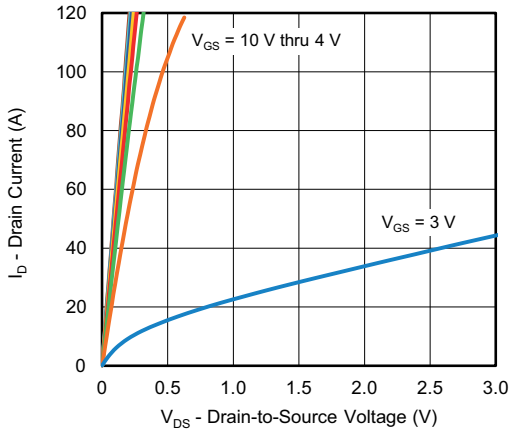
Notes

- a. Guaranteed by design, not subject to production testing
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$
- c. Based on characterization, not subject to production testing

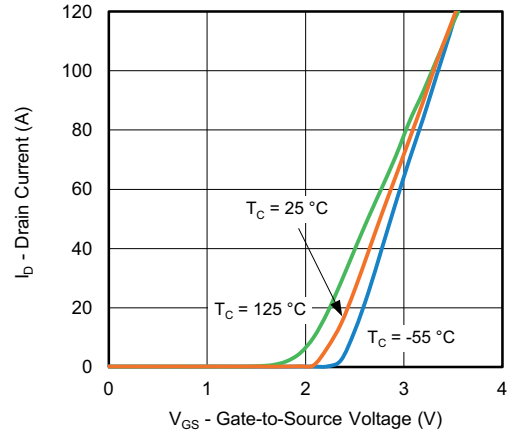
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



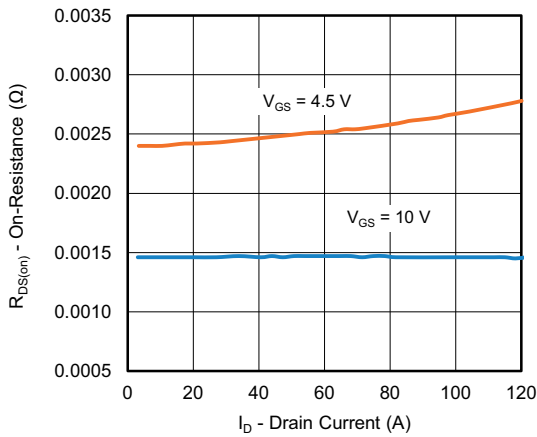
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



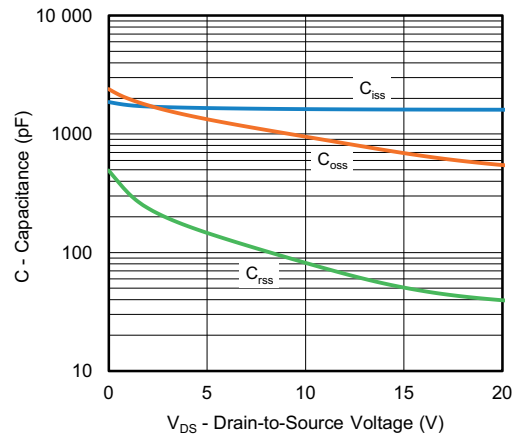
Output Characteristics



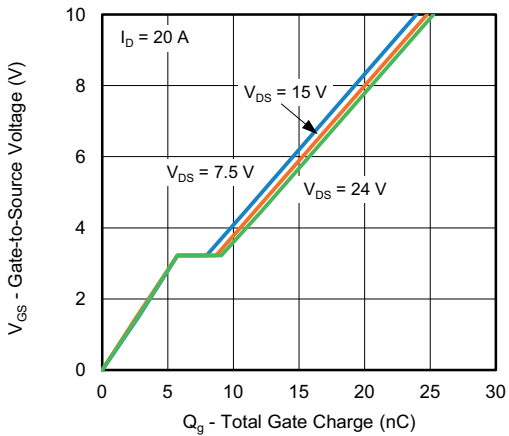
Transfer Characteristics



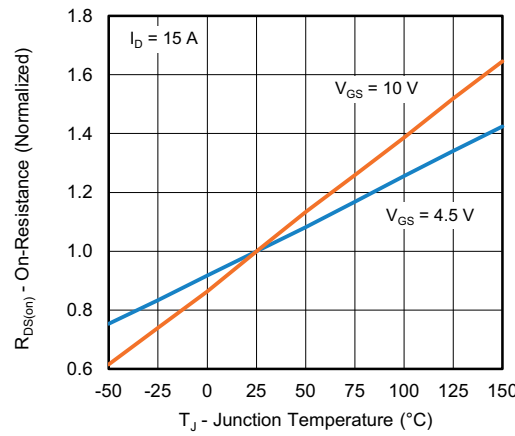
On-Resistance vs. Drain Current



Capacitance

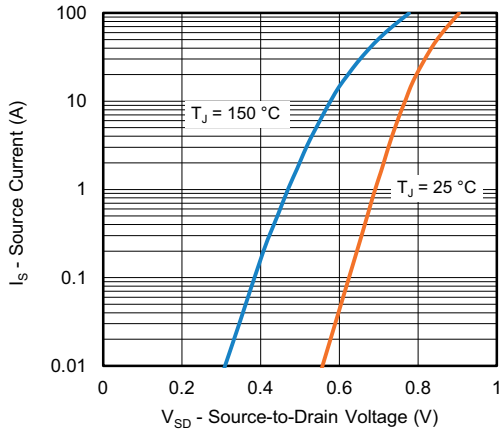


Gate Charge

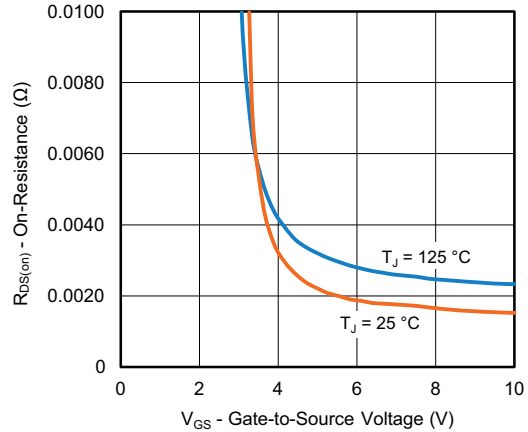


On-Resistance vs. Junction Temperature

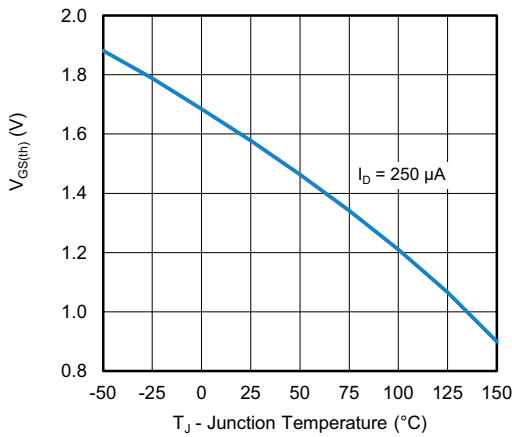
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



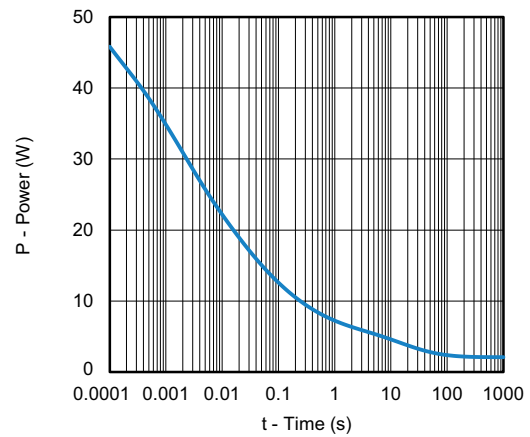
Source-Drain Diode Forward Voltage



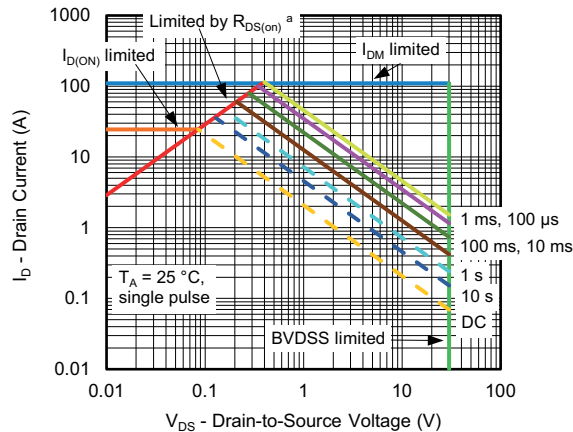
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



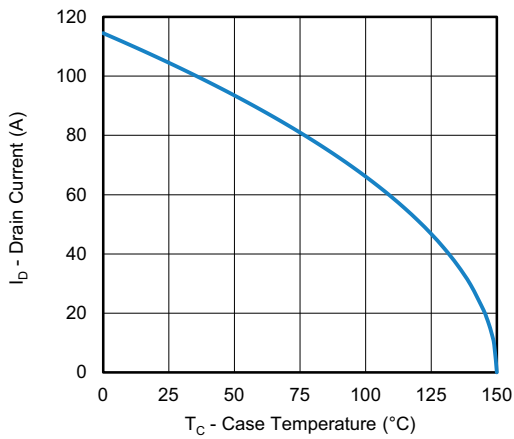
Safe Operating Area, Junction-to-Ambient

Note

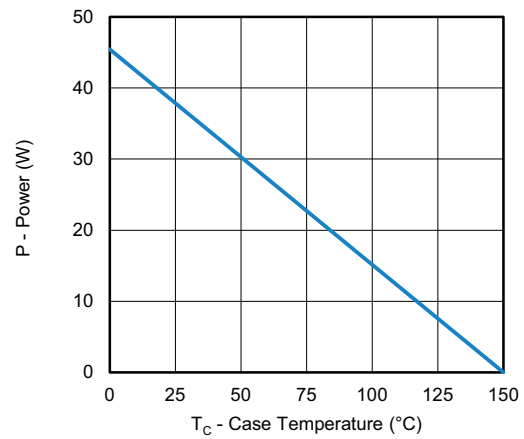
a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



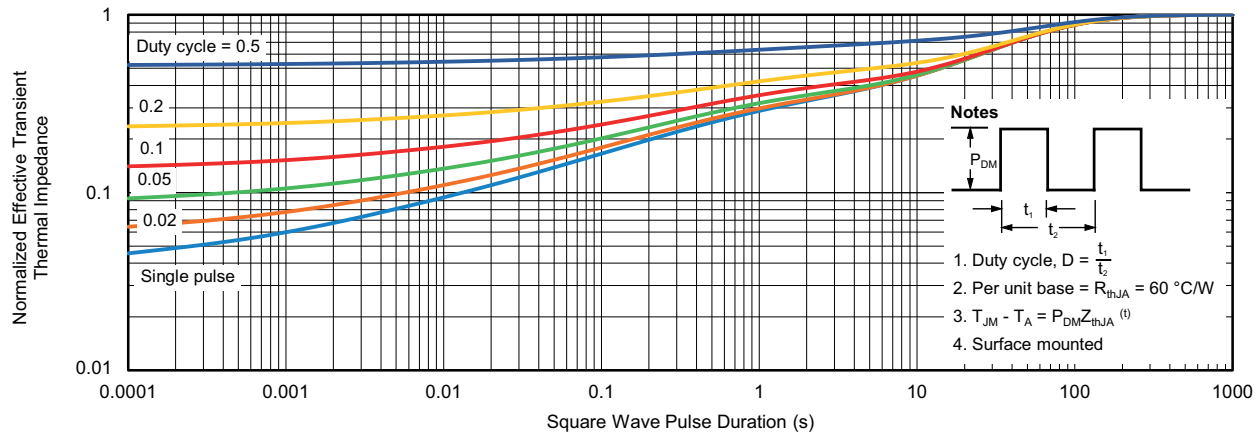
Power, Junction-to-Case

Note

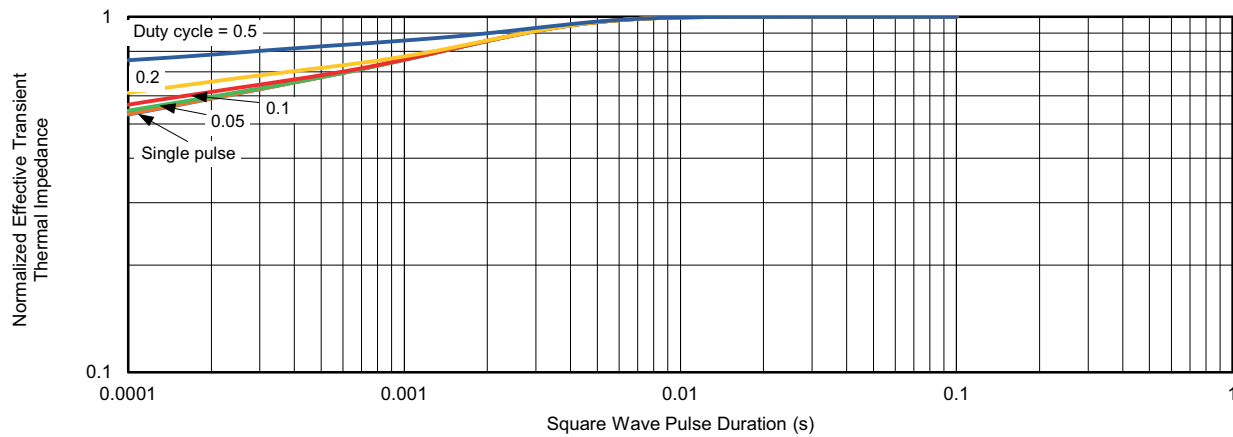
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

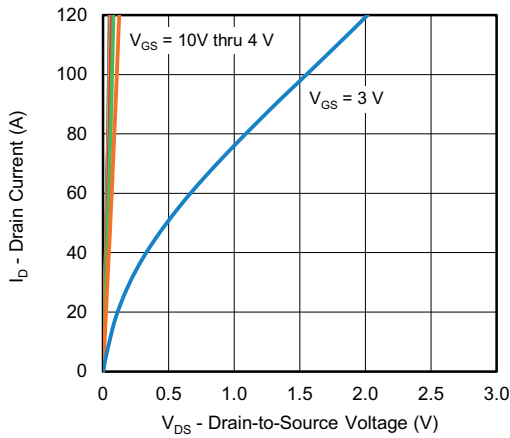


Normalized Thermal Transient Impedance, Junction-to-Ambient

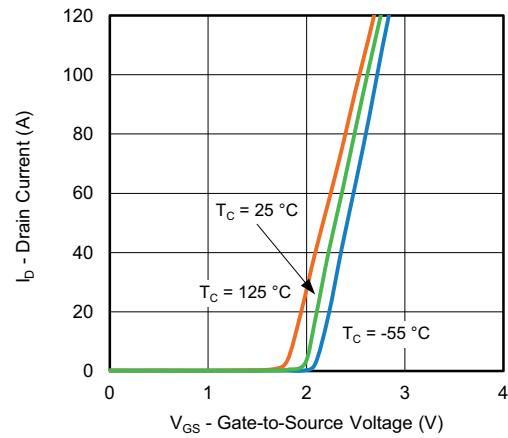


Normalized Thermal Transient Impedance, Junction-to-Case

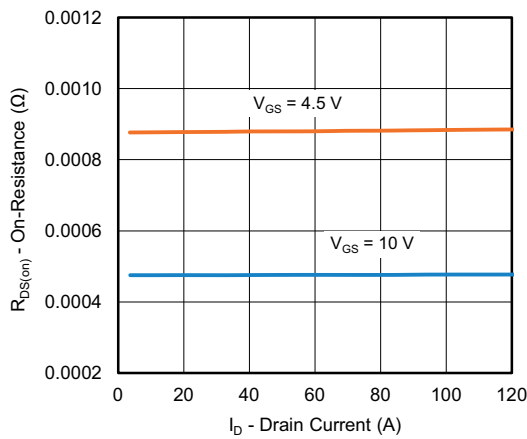
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



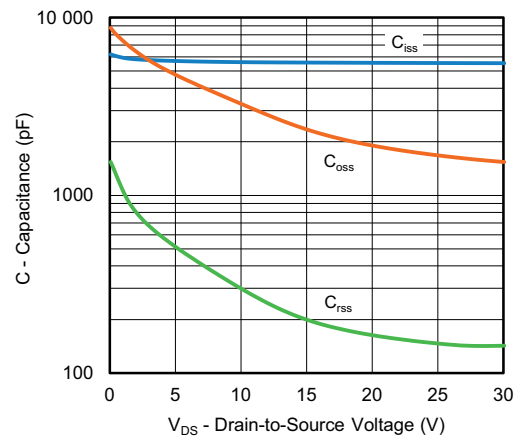
Output Characteristics



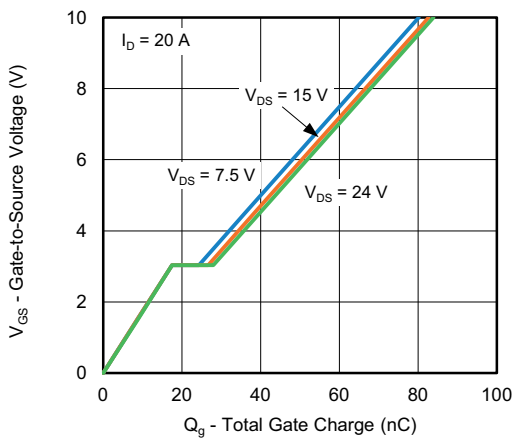
Transfer Characteristics



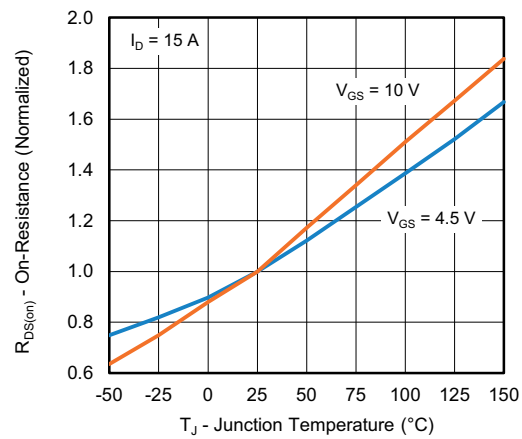
On-Resistance vs. Drain Current



Capacitance

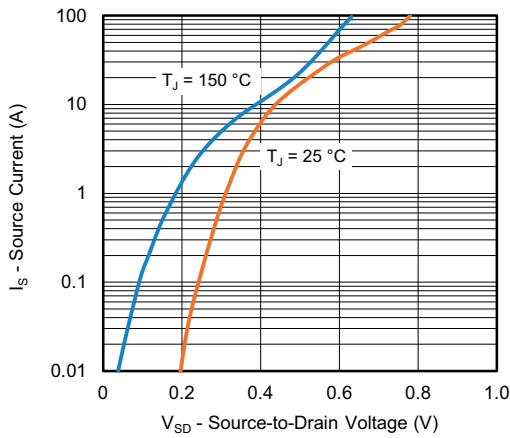


Gate Charge

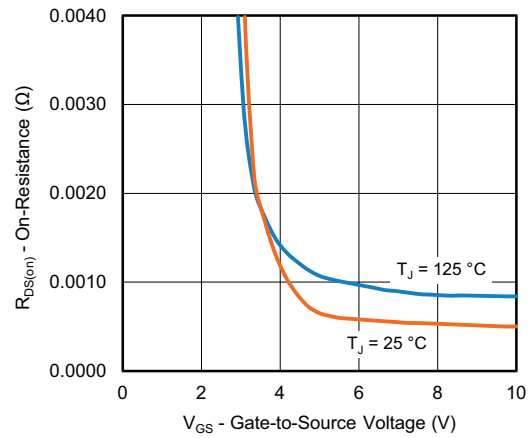


On-Resistance vs. Junction Temperature

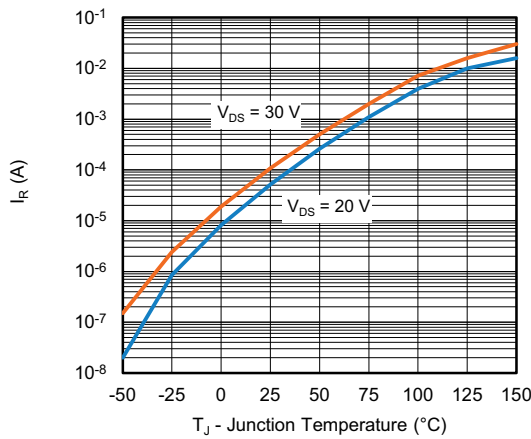
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



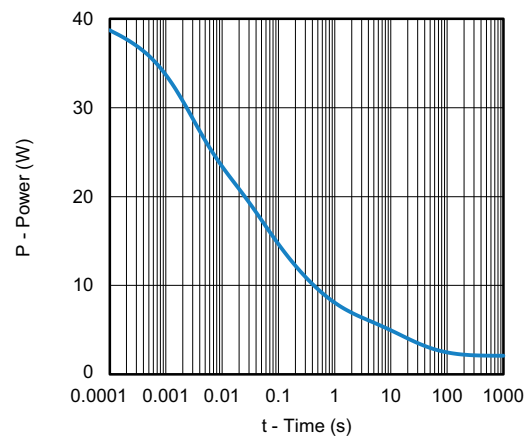
Source-Drain Diode Forward Voltage



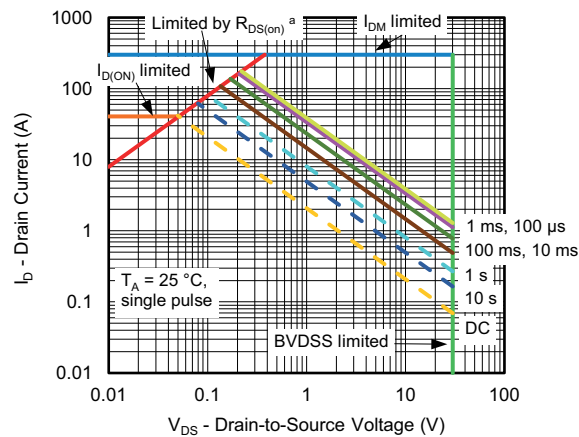
On-Resistance vs. Gate-to-Source Voltage



Reverse Current (Schottky)



Single Pulse Power, Junction-to-Ambient



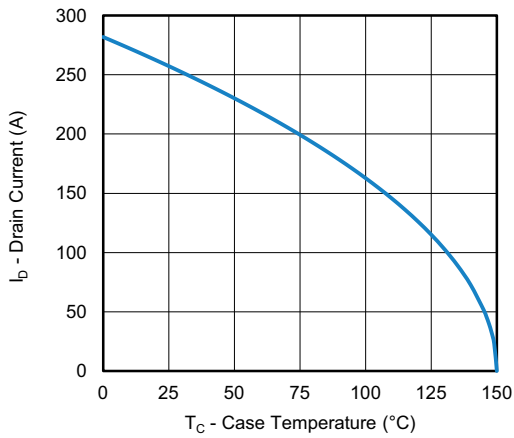
Safe Operating Area, Junction-to-Ambient

Note

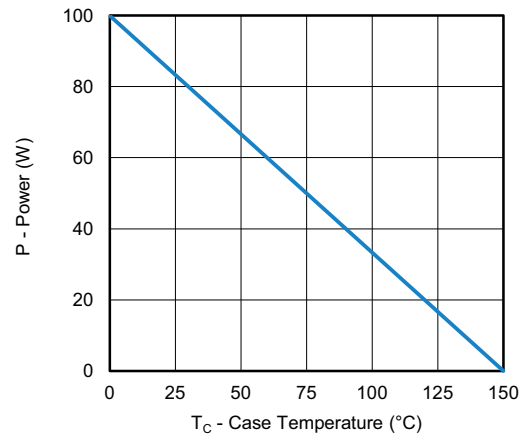
- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



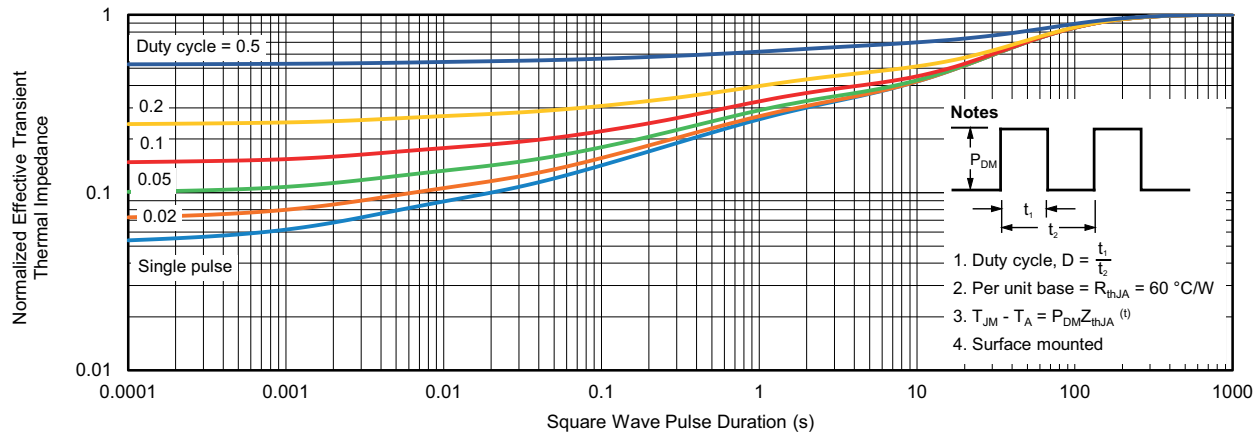
Power, Junction-to-Case

Note

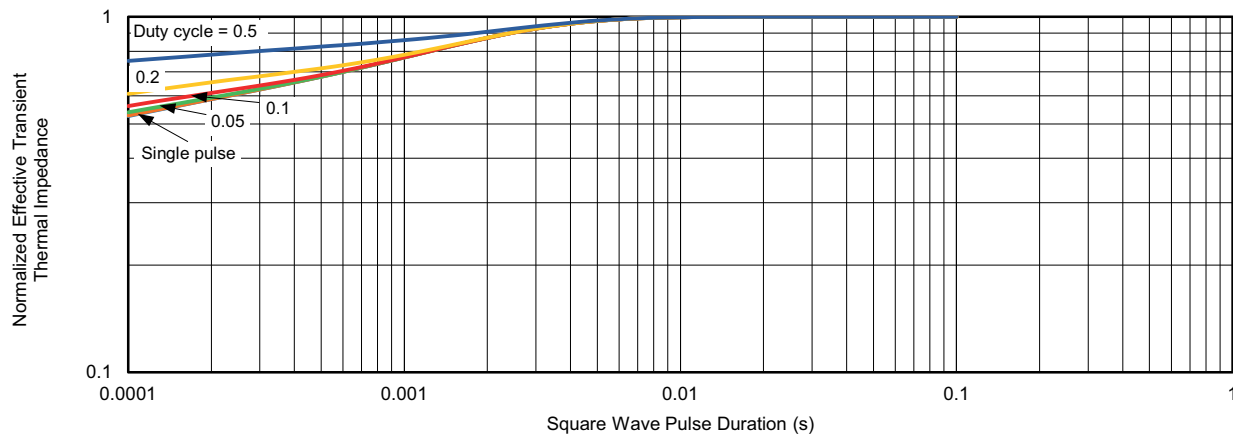
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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